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Manufacturers of World Class Discrete Semiconductors

2N3567 2N3568 2N3569 PN3567 PN3568 PN3569

JEDEC TO-105 JEDEC TO-92(EBC)

SILICON NPN TRANSISTORS

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3567, PN3567 Series types are Silicon NPN Small Signal Transistors designed for general purpose amplifier applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL	2N3568 PN3568	2N3567 PN3567 2N3569 PN3569	UNIT
Collector-Base Voltage	V_{CBO}	80	80	V
Collector-Emitter Voltage	V_{CEO}	60	40	V
Emitter-Base Voltage	V_{EBO}	5.0	5.0	V
Collector Current	I_C	500	500	mA
Base Current	I_B	100	100	mA
Power Dissipation, PN Types (TO-92 Case)	P_D	625		mW
Power Dissipation, 2N Types (TO-105 Case)	P_D	350		mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-55 TO +150		°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3567 PN3567 MIN	2N3567 PN3567 MAX	2N3568 PN3568 MIN	2N3568 PN3568 MAX	2N3569 PN3569 MIN	2N3569 PN3569 MAX	UNIT
I_{CBO}	V_{CB}=40V		50		50		50	nA
I_{CBO}	V_{CB}=40V, T_A=75°C		5.0		5.0		5.0	µA
I_{EBO}	V_{EB}=4.0V		25		25		25	nA
BV_{CBO}	I_C=100µA	80		80		80		V
BV_{CEO}	I_C=30mA	40		60		40		V
BV_{EBO}	I_E=10µA	5.0		5.0		5.0		V
$V_{CE(SAT)}$	I_C=150mA, I_B=15mA		0.25		0.25		0.25	V
$V_{BE(ON)}$	V_{CE}=1.0V, I_C=150mA		1.1		1.1		1.1	V
hFE	V_{CE}=1.0V, I_C=30mA	40		40		100		
hFE	V_{CE}=1.0V, I_C=150mA	40	120	40	120	100	300	
C_{ob}	V_{CB}=10V, f=140kHz		20		20		20	pF
C_{eb}	V_{EB}=0.5V, f=140kHz		80		80		80	pF
f_T	V_{CE}=10V, I_C=50mA, f=20MHz	60	600	60	600	60	600	MHz